MC74VHC1G14

Single Schmitt-Trigger Inverter

The MC74VHC1G14 is a single gate CMOS Schmitt−trigger inverter fabricated with silicon gate CMOS technology.

The internal circuit is composed of three stages, including a buffer output which provides high noise immunity and stable output.

The MC74VHC1G14 input structure provides protection when voltages up to 7 V are applied, regardless of the supply voltage. This allows the MC74VHC1G14 to be used to interface 5 V circuits to 3 V circuits.

The MC74VHC1G14 can be used to enhance noise immunity or to square up slowly changing waveforms.

Features

- High Speed: t_{PD} = 4 ns (Typ) at V_{CC} = 5 V
- Low Power Dissipation: I_{CC} = 1.0 μA (Max) at T_A = 25°C
- Power Down Protection Provided on Inputs
- Balanced Propagation Delays
- Pin and Function Compatible with Other Standard Logic Families
- Chip Complexity: FETs = 101
- Pb−Free Packages are Available

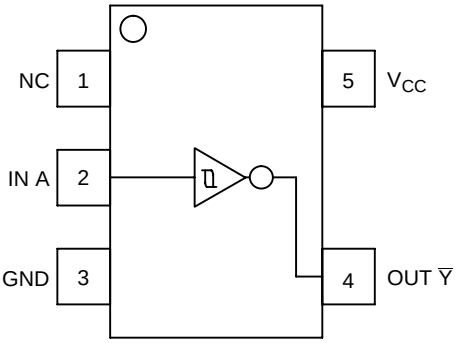

Figure 1. Pinout (Top View)

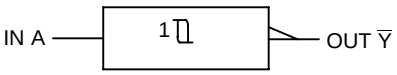

Figure 2. Logic Symbol

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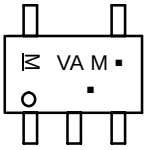
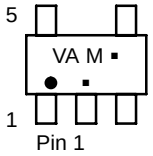
http://onsemi.com

MARKING DIAGRAMS



SC70−5/SC−88A/SOT−353
DF SUFFIX
CASE 419A



SOT23−5/TSOP−5/SC59−5
DT SUFFIX
CASE 483

VA = Device Code
M = Date Code*
▪ = Pb−Free Package

(Note: Microdot may be in either location)
*Date Code orientation and/or position may vary depending upon manufacturing location.

PIN ASSIGNMENT

1	NC
2	IN A
3	GND
4	OUT $\overline{Y}$
5	V_{CC}

FUNCTION TABLE

A Input	$\overline{Y}$ Output
L	H
H	L

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

MAXIMUM RATINGS

Symbol	Parameter		Value	Unit
V_{CC}	DC Supply Voltage		−0.5 to +7.0	V
V_{IN}	DC Input Voltage		−0.5 to +7.0	V
V_{OUT}	DC Output Voltage		−0.5 to V_{CC} +0.5	V
I_{IK}	DC Input Diode Current		−20	mA
I_{OK}	DC Output Diode Current		±20	mA
I_{OUT}	DC Output Sink Current		±12.5	mA
I_{CC}	DC Supply Current per Supply Pin		±25	mA
T_{STG}	Storage Temperature Range		−65 to +150	°C
T_L	Lead Temperature, 1 mm from Case for 10 Seconds		260	°C
T_J	Junction Temperature Under Bias		+150	°C
θ_{JA}	Thermal Resistance	SC70−5/SC−88A (Note 1) TSOP−5	350 230	°C/W
P_D	Power Dissipation in Still Air at 85°C	SC70−5/SC−88A TSOP−5	150 200	mW
MSL	Moisture Sensitivity		Level 1	
F_R	Flammability Rating	Oxygen Index: 28 to 34	UL 94 V−0 @ 0.125 in	
V_{ESD}	ESD Withstand Voltage	Human Body Model (Note 2) Machine Model (Note 3) Charged Device Model (Note 4)	>2000 >200 N/A	V
$I_{Latchup}$	Latchup Performance	Above V_{CC} and Below GND at 125°C (Note 5)	±500	mA

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Measured with minimum pad spacing on an FR4 board, using 10 mm−by−1 inch, 2−ounce copper trace with no air flow.
2. Tested to EIA/JESD22−A114−A.
3. Tested to EIA/JESD22−A115−A.
4. Tested to JESD22−C101−A.
5. Tested to EIA/JESD78.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter		Min	Max	Unit
V_{CC}	DC Supply Voltage		2.0	5.5	V
V_{IN}	DC Input Voltage		0.0	5.5	V
V_{OUT}	DC Output Voltage		0.0	V_{CC}	V
T_A	Operating Temperature Range		−55	+125	°C
t_r , t_f	Input Rise and Fall Time	V_{CC} = 3.3 V ± 0.3 V V_{CC} = 5.0 V ± 0.5 V	− −	No Limit No Limit	ns/V

Device Junction Temperature versus Time to 0.1% Bond Failures

Junction Temperature °C	Time, Hours	Time, Years
80	1,032,200	117.8
90	419,300	47.9
100	178,700	20.4
110	79,600	9.4
120	37,000	4.2
130	17,800	2.0
140	8,900	1.0

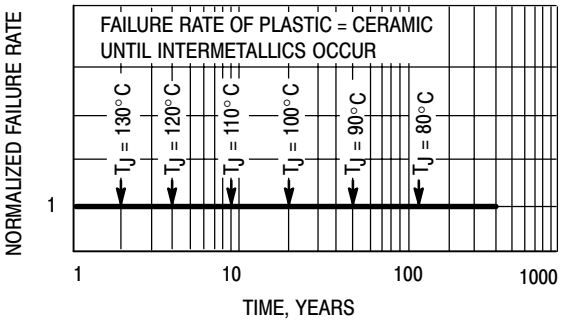


Figure 3. Failure Rate vs. Time Junction Temperature

DC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Test Conditions	V_{CC} (V)	T_A = 25°C			$T_A \le$ 85°C		−55 ≤ $T_A \le$ 125°C		Unit
				Min	Typ	Max	Min	Max	Min	Max	
V_{T+}	Positive Threshold Voltage		3.0 4.5 5.5	1.85 2.86 3.50	2.0 3.0 3.6	2.20 3.15 3.85		2.20 3.15 3.85		2.20 3.15 3.85	V
V_{T-}	Negative Threshold Voltage		3.0 4.5 5.5	0.9 1.35 1.65	1.5 2.3 2.9	1.65 2.46 3.05	0.9 1.35 1.65		0.9 1.35 1.65		V
V_H	Hysteresis Voltage		3.0 4.5 5.5	0.30 0.40 0.50	0.57 0.67 0.74	1.20 1.40 1.60	0.30 0.40 0.50	1.20 1.40 1.60	0.30 0.40 0.50	1.20 1.40 1.60	V
V_{OH}	Minimum High−Level Output Voltage	$V_{IN} \le V_T$ − Min I_{OH} = −50 μA	2.0 3.0 4.5	1.9 2.9 4.4	2.0 3.0 4.5		1.9 2.9 4.4		1.9 2.9 4.4		V
		I_{OH} = −4 mA I_{OH} = −8 mA	3.0 4.5	2.58 3.94			2.48 3.80		2.34 3.66		V
V_{OL}	Maximum Low−Level Output Voltage	$V_{IN} \ge V_T$ + Max I_{OL} = 50 μA	2.0 3.0 4.5		0.0 0.0 0.0	0.1 0.1 0.1		0.1 0.1 0.1		0.1 0.1 0.1	V
		I_{OL} = 4 mA I_{OL} = 8 mA	3.0 4.5			0.36 0.36		0.44 0.44		0.52 0.52	V
I_{IN}	Maximum Input Leakage Current	V_{IN} = 5.5 V or GND	0 to 5.5			±0.1		±1.0		±1.0	μA
I_{CC}	Maximum Quiescent Supply Current	$V_{IN} = V_{CC}$ or GND	5.5			1.0		20		40	μA

AC ELECTRICAL CHARACTERISTICS Input $t_r = t_f$ = 3.0 ns

Symbol	Parameter	Test Conditions	T_A = 25°C			$T_A \le$ 85°C		−55 ≤ $T_A \le$ 125°C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
t_{PLH}, t_{PHL}	Maximum Propagation Delay, A to $\overline{Y}$	V_{CC} = 3.3 ± 0.3 V C_L = 15 pF C_L = 50 pF		7.0 8.5	12.8 16.3	1.0 1.0	15.0 18.5	1.0 1.0	17.0 20.5	ns
		V_{CC} = 5.0 ± 0.5 V C_L = 15 pF C_L = 50 pF		4.0 5.5	8.6 10.6	1.0 1.0	10.0 12.0	1.0 1.0	11.5 13.5	
C_{IN}	Maximum Input Capacitance			5	10		10		10	pF

		Typical @ 25°C, V_{CC} = 5.0 V	
C_{PD}	Power Dissipation Capacitance (Note 6)	7.0	pF

6. C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: $I_{CC(OPR)} = C_{PD} \bullet V_{CC} \bullet f_{in} + I_{CC}$. C_{PD} is used to determine the no−load dynamic power consumption; $P_D = C_{PD} \bullet V_{CC}^2 \bullet f_{in} + I_{CC} \bullet V_{CC}$.

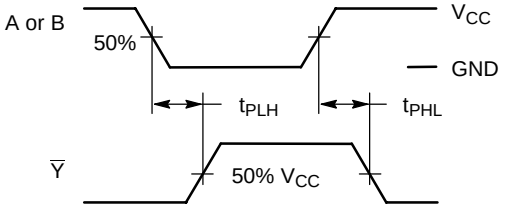
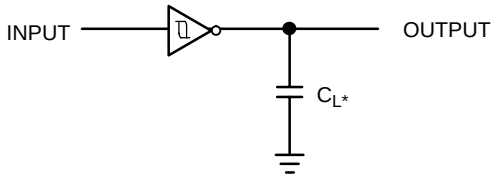


Figure 4. Switching Waveforms



*Includes all probe and jig capacitance.
A 1−MHz square input wave is recommended for propagation delay tests.

Figure 5. Test Circuit

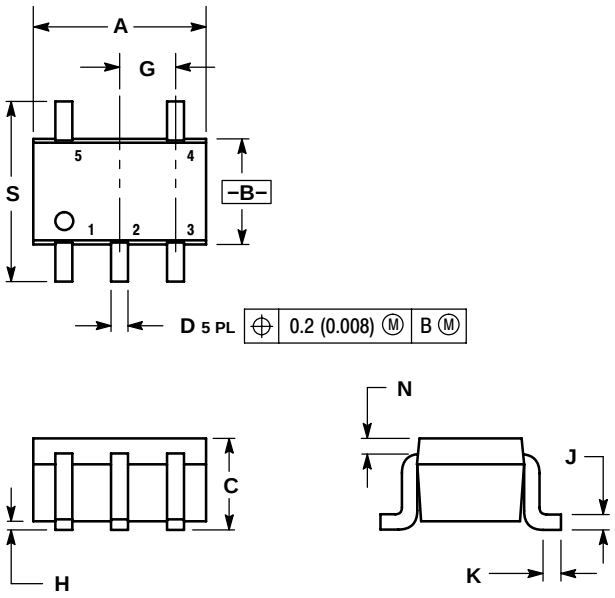
ORDERING INFORMATION

Device	Package	Shipping†
MC74VHC1G14DFT1	SC−88A/SOT−353	3000/Tape & Reel
MC74VHC1G14DFT1G	SC−88A/SOT−353 (Pb−Free)	
MC74VHC1G14DFT2	SC−88A/SOT−353	
MC74VHC1G14DFT2G	SC−88A/SOT−353 (Pb−Free)	
MC74VHC1G14DTT1	SOT−23/TSOP−5	
MC74VHC1G14DTT1G	SOT−23/TSOP−5 (Pb−Free)	

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

PACKAGE DIMENSIONS

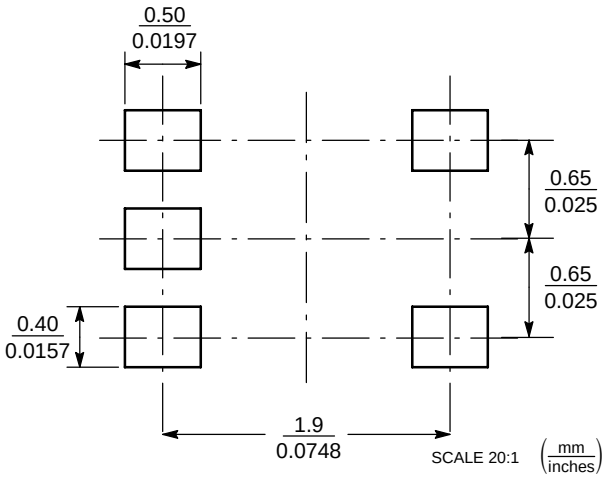
SC−88A, SOT−353, SC−70
CASE 419A−02
ISSUE J



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. 419A−01 OBSOLETE. NEW STANDARD 419A−02.
4. DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.071	0.087	1.80	2.20
B	0.045	0.053	1.15	1.35
C	0.031	0.043	0.80	1.10
D	0.004	0.012	0.10	0.30
G	0.026 BSC		0.65 BSC	
H	---	0.004	---	0.10
J	0.004	0.010	0.10	0.25
K	0.004	0.012	0.10	0.30
N	0.008 REF		0.20 REF	
S	0.079	0.087	2.00	2.20

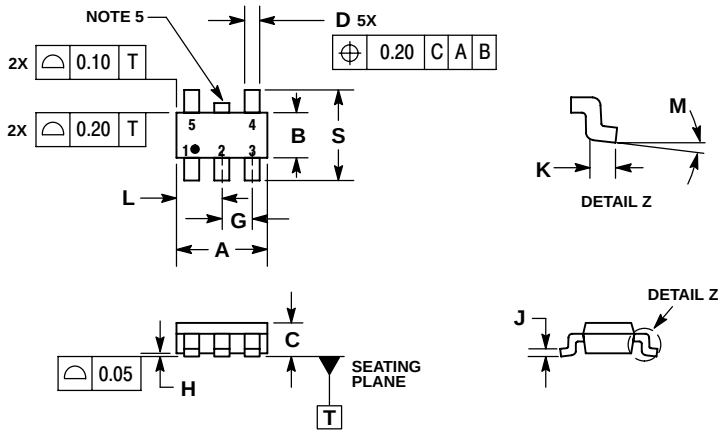
SOLDERING FOOTPRINT*



*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

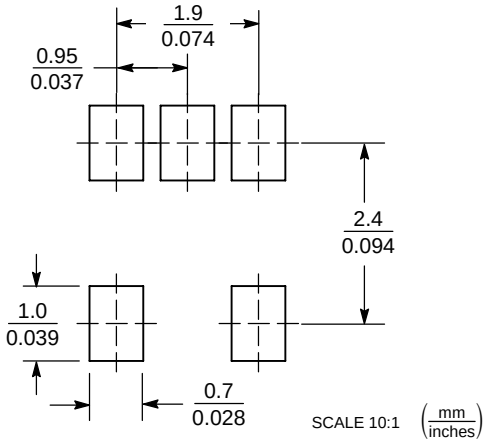
TSOP−5
CASE 483−02
ISSUE F



NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.
5. OPTIONAL CONSTRUCTION: AN ADDITIONAL TRIMMED LEAD IS ALLOWED IN THIS LOCATION. TRIMMED LEAD NOT TO EXTEND MORE THAN 0.2 FROM BODY.

	MILLIMETERS	
DIM	MIN	MAX
A	3.00 BSC	
B	1.50 BSC	
C	0.90	1.10
D	0.25	0.50
G	0.95 BSC	
H	0.01	0.10
J	0.10	0.26
K	0.20	0.60
L	1.25	1.55
M	0 °	10 °
S	2.50	3.00

SOLDERING FOOTPRINT*



*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Literature Distribution Center for ON Semiconductor
P.O. Box 5163, Denver, Colorado 80217 USA
Phone: 303−675−2175 or 800−344−3860 Toll Free USA/Canada
Fax: 303−675−2176 or 800−344−3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

N. American Technical Support: 800−282−9855 Toll Free USA/Canada
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For additional information, please contact your local Sales Representative

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